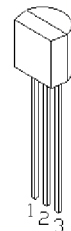


MICRO ELECTRONICS

MCR100-4A
MCR100-6A
MCR100-8A
0.8A SILICON
CONTROLLED
RECTIFIERS

- * Driven directly with IC and MOS device.
- * Feature proprietary, void-free glass passivated chips.
- * Available in voltage ratings from 100 to 600 volts (VDRM and VRRM)
- * Sensitive gate trigger current.
- * Designed for high volume, line-powered control application in relay lamp drivers, small motor controls, gate drivers for large thyristors.

TO-92

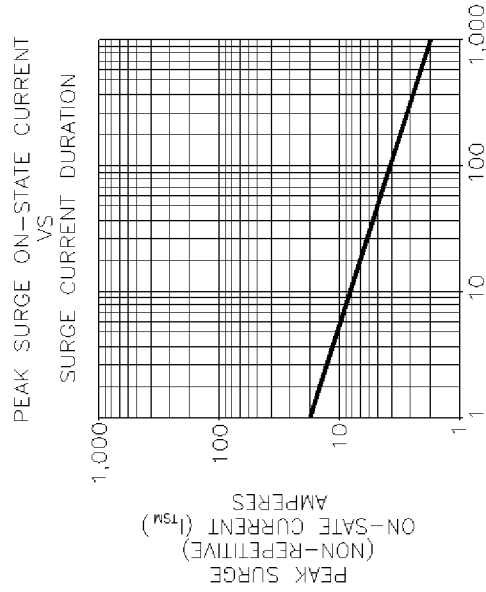


Pin 1 : Cathode
 Pin 2 : Anode
 Pin 3 : Gate

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

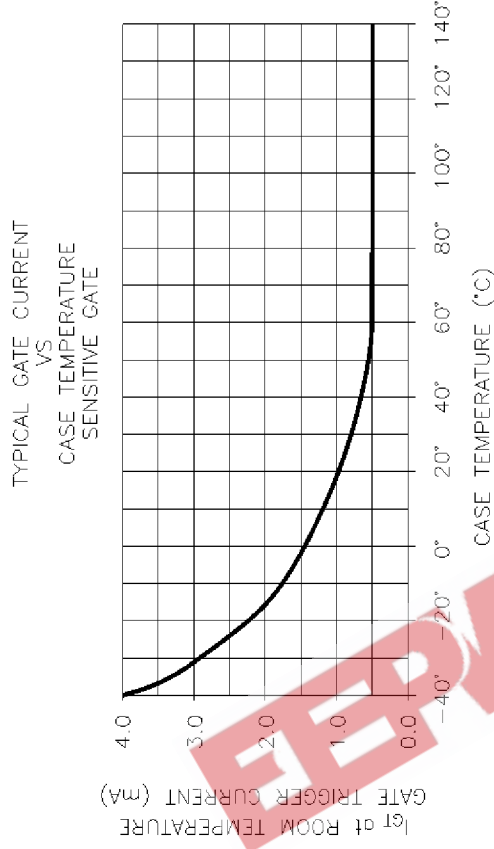
PARAMETER	SYMBOL	DEVICE NUMBERS		UNITS
Repetitive Peak Off-State Voltage and Repetitive Peak Reverse Voltage and Tc=125°C	VDRM & VRRM	MCR100-4A MCR100-6A MCR100-8A	200 400 600	V
RMS On-State Current at Tc=50°C and Conduction Angle of 180°	IT (RMS)		0.8	A
Peak Surge (Non-Repetitive) On-State Current, One-Cycle, at 50Hz or 60Hz	ITSM		8	A
Peak Gate-Trigger Current for 3µ sec. Max.	IGTM		0.8	A
Peak Gate-Power Dissipation at IGT ≤ or = IGTM	PGM		5	W
Average Gate-Power Dissipation	PG(AV)		0.2	W
Peak Off-State Current (1) Tc=25°C	IDRM & IRRM		10 200	µA MAX
VDRM & VRRM = Max. Rating Tc=125°C				
Maximum On-State Voltage. (Peak) at Tc=25°C and IT= Rated Amps	VTM		1.7	V MAX
DC Holding Current, (1) Tc=25°C	IHO		5	mA MAX
Critical Rate-Of-Rise of Off-State Voltage. (1) Gate Open, Tc=110°C	Critical dv/dt		5	V/µ sec
DC Gate-Trigger Current for Anode Voltage = 7V DC, RL = 100 ohm and at Tc=25°C	IGT		200	µA MAX
Storage Temperature Range	Tstg		-40 to +150	°C
Operating Temperature Range, Tc	Tamb		-40 to +110	°C

MCR100-4A 6A 8A



SURGE CURRENT DURATION, FULL CYCLES at 60Hz
CURRENT WAVEFORM : SINUSOIDAL, 60Hz
RESISTIVE LOAD

1. MEASURED AT HOTTEST POINT
2. WAVEFORM : SINUSOIDAL, 50Hz to 60Hz 140°
3. 180° CONDUCTION



MAXIMUM ALLOWABLE CASE TEMPERATURE VS ON-STATE CURRENT



MAXIMUM CONDUCTION POWER DISSIPATION VS ON-STATE CURRENT

